

AMENDMENTS TO THE CLAIMS

This listing of claims will replace all prior versions, and listings, of claims in the present application:

Listing of Claims:

1. **(Previously Presented)** A light emitting device comprising
a semiconductor light emitting component; and
a phosphor capable of absorbing a part of light emitted by the light emitting component
and emitting light of wavelength different from that of the absorbed light,

wherein a straight line connecting a point of chromaticity corresponding to a spectrum
generated by the light emitting component and a point of chromaticity corresponding to a
spectrum generated by the phosphor is substantially along a black body radiation locus in a
chromaticity diagram.

2. **(Original)** The light emitting device according to claim 1,
wherein said light emitting component is a blue LED.

3. **(Previously Presented)** The light emitting device according to claim 1,
wherein said point of chromaticity corresponding to the spectrum generated by the light
emitting component, said point of chromaticity corresponding to the spectrum generated by the
phosphor and contents of the phosphor are adjusted so that said straight line is along with the
black body radiation locus.

4. **(Previously Presented)** The light emitting device according to claim 1,
wherein said straight line contains a point corresponding to a color temperature of about 8080K or 4400K.

5. **(Canceled)**

6. **(Previously Presented)** The light emitting device according to claim 1,
wherein a main emission peak of the light emitting component is set within the range from about 420 nm to 490 nm.

7. **(Previously Presented)** The light emitting device according to claim 1,
wherein a main emission peak of the light emitting component is set within the range from about 450 nm to 475 nm.

8. **(Original)** The light emitting device according to claim 1,
wherein the structure of the light emitting component is either one structure of homostructure, heterostructure and double-heterostructure which have MIS junction, PIN junction or PN junction.

9. **(Original)** The light emitting device according to claim 1,
wherein said light emitting component comprises an active layer having a single quantum well structure or multi quantum well structure.

10. (**Currently Amended**) The light emitting device according to claim 1,
wherein said phosphor is made by steps of ~~solving~~ dissolving rare earth elements in acid in stoichiometrical proportions, coprecipitating the solution with oxalic acid to obtain a sediment, firing the sediment to obtain an oxide, and firing a mixture of said oxide, an ammonium fluoride and aluminum oxide.

11. (**Previously Presented**) The light emitting device according to claim 1,
wherein an emission peak of the phosphor is set within the range from about 530 nm to 570 nm.

12. (**Previously Presented**) The light emitting device according to claim 1,
wherein an emission peak of the phosphor is set within the range from about 510 nm to 600 nm.

13. (**Previously Presented**) The light emitting device according to claim 1,
wherein the spectrum generated by the phosphor is mixed light generated by at least two different phosphors.

14. (**Previously Presented**) The light emitting device according to claim 1,
wherein an active layer of the semiconductor light emitting component comprises InGaN.

15. **(Previously Presented)** The light emitting device according to claim 14, wherein an amount of In element of the active layer is adjusted, and/or a composition rate of phosphor is adjusted.

16. **(Previously Presented)** A light emitting device comprising:
a semiconductor light emitting component; and
a phosphor capable of absorbing a part of light emitted by the light emitting component and emitting light of wavelength different from that of the absorbed light,
wherein a straight line connecting a point of chromaticity along an emission wavelength corresponding to a spectrum generated by the light emitting component and a point of chromaticity along an emission wavelength corresponding to a spectrum generated by the phosphor corresponds to white light substantially along a black body radiation locus in a chromaticity diagram.

17. **(New)** A method of making a light emitting device, said light emitting device comprising said semiconductor light emitting component and a phosphor capable of absorbing a part of light emitted by the light emitting component and emitting light of wavelength different from that of the absorbed light, wherein a straight line connecting a point of chromaticity corresponding to a spectrum generated by the light emitting component and a point of chromaticity corresponding to a spectrum generated by the phosphor is substantially along a black body radiation locus in a chromaticity diagram; said method comprising:

adjusting an amount of an In element of an active layer of the semiconductor light emitting component, and/or adjusting a composition rate of the phosphor in said light emitting device;

wherein said semiconductor light emitting component comprises a nitride compound semiconductor.

18. (New) The method of making a light emitting device of claim 17, wherein said phosphor is made by the steps of:

dissolving rare earth elements in acid in stoichiometrical proportions,
coprecipitating the solution with oxalic acid to obtain a sediment,
firing the sediment to obtain an oxide, and
firing a mixture of said oxide, an ammonium fluoride and aluminum oxide.